

Type	Hits	Ref	Search Text	DBs	Time Stamp
BRS	115918	S895	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/23/05
BRS	122262	S944	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	86	S945	S944 and EWMA	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	85	S946	S945 and control\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	53	S947	S946 and predict\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	14	S948	S947 and (target same result)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	122262	S950	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	122262	S951	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	86	S952	S951 and EWMA	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	85	S953	S952 and control\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	53	S954	S953 and predict\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	14	S955	S954 and (target same result)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
IS&R	100	S957	((4946803') or ('4965872') or ('5851880') or ('43373249') or ('4435897') or ('4471373') or ('4502069') or ('4612480') or ('4764479') or ('4796194') or ('4888536') or ('4894699') or ('5015601') or ('5233559') or ('5296727') or ('5367185') or ('5394360') or ('5399519') or ('5445987') or ('5464783') or ('5610420') or ('5612238') or ('5656510') or ('5661043') or ('5675140') or ('5677475') or ('5686362') or ('5751757') or ('57657543') or ('5801383') or ('5808943') or ('5817556') or ('5837584') or ('5886468') or ('5886377') or ('5888296') or ('5896314') or ('5940299') or ('5955895') or ('5959888') or ('5963810') or ('5963808') or ('5962893') or ('5970383') or ('5973341') or ('5974816') or ('5985716') or ('6069401').PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	122262	S958	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	122262	S959	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	86	S960	S959 and EWMA	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	85	S961	S960 and control\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	53	S962	S961 and predict\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	14	S963	S962 and (target same result)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	122262	S964	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	122262	S965	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	88	S966	S965 and EWMA	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	85	S967	S966 and control\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	53	S968	S967 and predict\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	14	S969	S968 and (target same result)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	3307	S972	(700/26 or 700/31 or 700/17 or 700/121 or 700/97).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	1383	S973	(702/30 or 702/120 or 702/109 or 702/189 or 702/193).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	2234	S974	(438/5 or 438for.101 or 438for.141 or 438for.142).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	6844	S975	S972 or S973 or S974	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	1622	S976	S975 and (semiconductor same manufact\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	923	S977	S976 and (process same control)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	181	S978	S977 and ((target or desired or threshold)same result)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	109	S979	S978 and (input and output)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	71	S980	S979 and relationship	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	1	S981	S980 and emwa	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	0	S983	S957 and EMWA	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	20	S984	S957 and (semiconductor near manufacturing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	8	S985	S984 and (process same control)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	0	S986	S985 and (input near data)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	2	S988	emwa and (semiconductor near manufacturing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	2	S989	emwa and (semiconductor same manufacturing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	2	S990	emwa and (semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	15	S949	S947 and ((target same result) or (target same outcome))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	15	S956	S954 and (target same result) or (target same outcome))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	15	S970	S962 and ((target same result) or (target same outcome))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	15	S971	S968 and ((target same result) or (target same outcome))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	24	S982	S980 and filter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	3	S987	S985 and (input and output)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	122262	S943	semiconductor near manufacturing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	17410	S991	S943 and (process same control)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	17410	S992	S944 and (process same control)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	1281	S993	S992 and predict\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	925	S994	S993 and minim\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	925	S995	S994 and control\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	239	S996	S995 and (set\$4 same target)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	2775	S997	(702/109 or 702/127 or 702/182 or 702/189 or 702/190 or 702/193-194).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	5940	S998	(438/10 or 438/14 or 438/17).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	324	S999	(219/490).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	2883	S1000	(700/19 or 700/28-29 or 700/32).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	11863	S1001	S997 or S998 or S999 or S1000	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	1047	S1002	S1001 and S944	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	482	S1003	S1002 and (minim\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	0	S1004	S1003 and emwa	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
BRS	36	S1005	S1003 and (moving near average)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/22/05
IS&R	2	S1006	("20050221514").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/23/05
BRS	1	S1007	S1006 and linear	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/23/05
BRS	1	S1008	S1006 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/23/05
BRS	1	S1009	S1006 and contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/23/05
IS&R	2	S1010	("20050221514").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/23/05
BRS	1	S1011	S1010 and (multiple same process)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/23/05